R&D for R3B/EXL silicon spectrometers, ELISe in-ring instrumentation based on planar Si and CVDD

Alexander Gorshkov

Flerov Laboratory of Nuclear Reactions Joint Institute for Nuclear Research Dubna, Russia

FAIR: Facility for Antiproton and Ion Research



^{*} W. Henning, NuSTAR Meeting

R3B: Reactions with Relativistic Radioactive Beams



Schematic drawing of the experimental setup comprising γ-ray and target recoil detection, a largeacceptance dipole magnet, a high-resolution magnetic spectrometer, neutron and light-charged particle detectors, and a variety of heavy-ion detectors

EXL: EXotic Nuclei Studied in Light-Ion Induced Reaction at the NESR



Completely new setup: Si shell (~ 700 items) CsI shell (~ 2000 items)

PTI (St.Petersburg) – silicon detectors VNIIEF (Sarov) – mechanical support & temperature stabilization system JINR and Kurchatov Institute – CsI shell JINR – in-ring instrumentation

The EXL Recoil and Gamma Array



• Thin Si DSSD $\rightarrow \Delta E, x, y$

≤100 µm thick, spatial resolution better than 500 µm, ΔE ≈30 keV (FWHM)

• Si DSSD \rightarrow tracking

300 μ m thick, double sided, spatial resolution better than 100 μ m, $\Delta E \approx 30 \text{ keV}$ (FWHM)

• Si(Li) \rightarrow E

9 mm thick, large area 100*100 mm², ΔE ≈50 keV (FWHM)

• CsI crystals $\rightarrow \Delta E, \gamma$

high efficiency, high resolution, 20 cm thick

ELISe: ELectron-Ion Scattering experimet



BINP – deflection-separation magnets INR RAS & KI – electron spectrometer & luminosity monitor JINR – in ring instrumentation & simulation

R&D status aimed on in-ring instrumentation for EXL/ELISe



Positions of detector arrays in the first bending section behind interaction zone in the NESR:

- @ detector array (1) in front of the first dipole magnet allowing for 'reaction tagging'
- * two arrays (2 and 3) placed after the first dipole magnet intended for fragment tracking together with array (1)
- G[™] detector array (4) placed in front of the quadrupole section to implement the same task for fragments showing $\Delta p/p \sim 1-2\%$

Electron-Ion Interaction Point

Reactions: e(0.5GeV) + ¹³²Sn(0.74 AGeV)

- elastic scattering

- inelastic scattering with excitation of

¹³²Sn(E=10MeV, Γ = 1MeV) \rightarrow ¹³¹Sn + n

NESR structure: version 65 with bypass:

- beta_X = 1.0m, beta_Y = 0.15m

- emittance_X(Y) = 0.05π mm mrad, Δ P/P=0.04%

- $\sigma(x) = 0.22$ mm, $\sigma(y) = 0.09$ mm

- $\Delta(\theta x) = \pm 0.22 \text{ mrad}, \Delta(\theta y) = \pm 0.58 \text{ mrad}$

TOF system parameters:

- TOF path = 7.2 m; $\sigma(TOF) = 50 \text{ ps}$

- $\Delta X(Y)$ accuracy of track position = 0.1 mm

- detector thicknesses = 0.3 mm of Silicon

Results of simulation



S. Stepantsov, ELISe Meeting 2009, Dubna

Request to detector system

- Detectors located nearby the circulating beam in the first two planes (arrays 1 and 2) should be thin enough in order to avoid any noticeable distortion caused by multiple scattering in the measured particle trajectories (100-300 µm @ UHV).
- High granularity strip detectors providing at least a 0.1 mm resolution for the ion hit positions.
- Very good timing resolution (σ ~ 30-50 ps) and acceptable energy resolution for one planes 1-3 (~0.5%).
- > Big enough active area $(X,Y \sim 30 \times 20 \text{ cm}^2)$ for arrays 3,4).
- The detector arrays in planes 1–4 should be subdivided into two halves, each one mounted on a remotely controlled driving device, since the detector can be positioned only after beam adjustments in the NESR is completed.

First results for CVDD & Si µ-strip detector



The typical pulses from CVDD in the case of ⁶Li ions (59 MeV) at the intensities of ~5x10⁷ pps.



GSI



The typical pulses from Si micro-strip detector irradiated by alpha source ²³⁸Pu (5.5 MeV).

PTI, St.Petersburg



ACCULINNA fragment separator at U-400M cyclotron



300 μ m thick, no backing





First results with RIB's for CVDD and SCD detectors



CVDD (blue) , SC (yellow) $\Rightarrow \delta t \sim 250 \text{ ps}$





identification plots for the reaction ¹⁵N(47 AMeV) + ¹²C @ E(⁶He) ~ 40 AMeV

Si μ -strip detector



1.5x1.5 mm², 300 μm thick,



backing





Advantages of Si over diamond:

- the same time resolution
- good amplitude resolution
- simplicity in operation
- not expensive
- ? radiation hardness

Thick round DSSD detector





64 sectors from the front side and 32 rings on the back side.

Active zone external diameter - 84 mm, internal diameter - 28 mm.

Distance between two neighboring sectors - 40 μ m. Distance between two rings – 170 μ m. Si wafer thickness is 1 mm.

Full depletion voltage U = 200 B, I \approx 2 μ A.

Thick round DSSD detector



Leading edge of signals have duration about 0.5-0.6 µs Energy resolution of sectors at room temperature 40 keV

Thick square DSSD detector





32 strips on the front and back sides. interstrip distance on the front side - 40 μ m, on the back side - 210 μ m. Active area 58×58 μ m², thickness of silicon wafer - 1 mm, Full depletion voltage U = 200 V, current I ≈ 1.2 μ A.

Thick square DSSD detector



Energy resolution of front stripes at room temperature 35 keV

Conclusion

SC diamond detectors:

- + good timing and energy resolutions
- + high radioactive hardness
- can't be big enough
- very expensive

CVD detectors:

- + good timing resolution
- + high radioactive hardness
- low energy resolution
- can't be produced big enough in the nearest some years

Si µ-strip detectors:

- + good timing and energy resolutions
- + low cost
- ? low radioactive hardness

Thick DSSD detectors:

- + perfect energy resolutions
- + low interstrip charge division
- not so fast, as Si µ-strip and diamond detectors
- ? low radioactive hardness